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Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	SIO, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	13
Program Memory Size	12KB (12K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	768 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21193dsp-	

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1.2 Performance Overview

Table 1.1 outlines the Functions and Specifications for R8C/18 Group and Table 1.2 outlines the Functions and Specifications for R8C/19 Group.

Table 1.1 Functions and Specifications for R8C/18 Group

Table 1.1 F	ltem	Specification
CPU	Number of fundamental	89 instructions
	instructions	
	Minimum instruction execution	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V)
	time	100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V)
	Operation mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to Table 1.3 Product Information for R8C/18
		Group
Peripheral	Ports	I/O ports: 13 pins (including LED drive port)
Functions		Input port: 3 pins
	LED drive ports	I/O ports: 4 pins
	Timers	Timer X: 8 bits × 1 channel, timer Z: 8 bits × 1 channel
		(Each timer equipped with 8-bit prescaler)
		Timer C: 16 bits × 1 channel
		(Input capture and output compare circuits)
	Serial interfaces	1 channel
	Cona monacc	Clock synchronous serial I/O, UART
		1 channel
		UART
	Comparator	1-bit comparator: 1 circuit, 4 channels
	Watchdog timer	15 bits × 1 channel (with prescaler)
	Waterlady times	Reset start selectable, count source protection mode
	Interrupts	Internal: 10 sources, External: 4 sources, Software: 4
	Interrupts	sources,
		Priority levels: 7 levels
	Clock generation circuits	2 circuits
	Clock generation should	Main clock oscillation circuit (with on-chip feedback
		resistor)
		On-chip oscillator (high speed, low speed)
		High-speed on-chip oscillator has frequency
		adjustment function
	Oscillation stop detection	Main clock oscillation stop detection function
	function	Wall Clock Oscillation stop detection function
	Voltage detection circuit	On-chip
	Power-on reset circuit	On-chip
Electric	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz)
Characteristics	Cappi, remage	VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz)
Gridiadionolio	Current consumption	Typ. 9 mA (VCC = 5.0 V, f(XIN) = 20 MHz, comparator stopped)
		Typ. 5 mA (VCC = $3.0V$, f(XIN) = 10 MHz, comparator stopped)
		Typ. 35 μ A (VCC = 3.0 V, wait mode, peripheral clock off)
		Typ. 0.7 μ A (VCC = 3.0 V, wait mode)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
I ladii Wollidiy	Programming and erasure	100 times
	endurance	100 111100
Operating Ambi	ent Temperature	-20 to 85°C
	on tomporatoro	-40 to 85°C (D version)
Package		20-pin molded-plastic LSSOP
. aonago		20-pin molded-plastic SDIP
		28-pin molded-plastic HWQFN
		1 - c Forded Praesie i i i d. i i

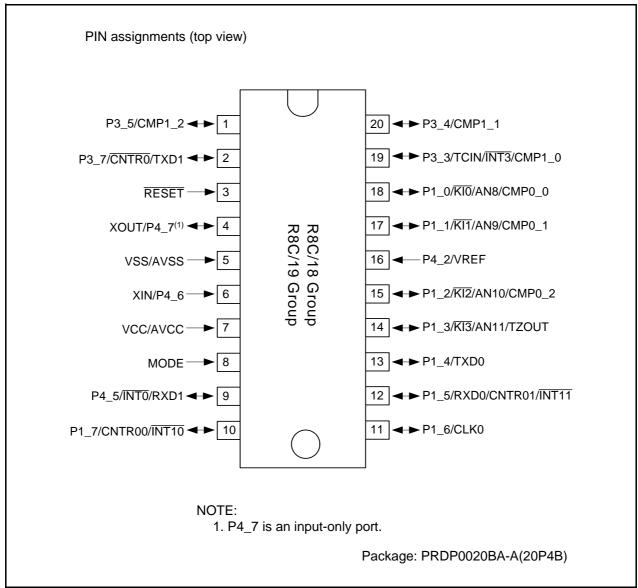


Figure 1.5 Pin Assignments for PRDP0020BA-A Package (Top View)

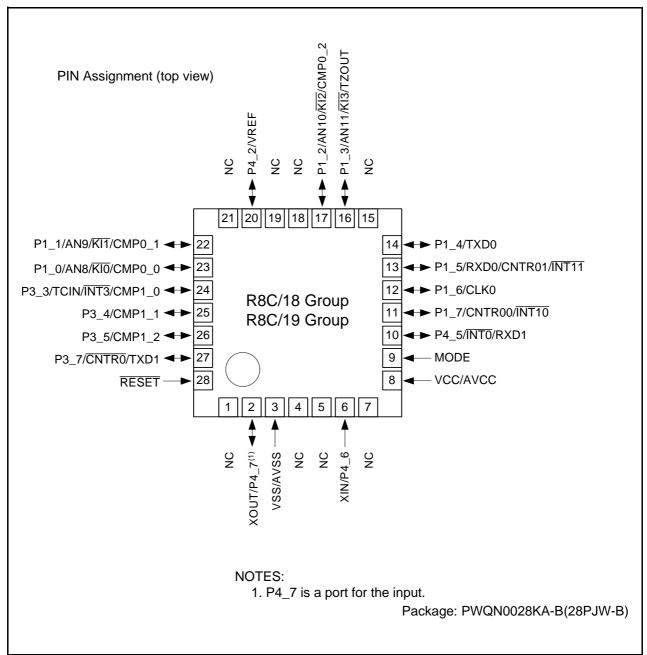


Figure 1.6 Pin Assignments for PWQN0028KA-B Package (Top View)

1.6 Pin Functions

Table 1.5 lists Pin Functions, Table 1.6 lists Pin Name Information by Pin Number of PLSP0020JB-A, PRDP0020BA-A packages, and Table 1.7 lists Pin Name Information by Pin Number of PWQN0028KA-B package.

Table 1.5 Pin Functions

Туре	Symbol	I/O Type	Description
Power supply input	VCC VSS	I	Apply 2.7 V to 5.5 V to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	I	Power supply for the comparator Connect a capacitor between AVCC and AVSS.
Reset input	RESET	I	Input "L" on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
Main clock input	XIN	I	These pins are provided for main clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins.
Main clock output	XOUT	0	To use an external clock, input it to the XIN pin and leave the XOUT pin open.
INT interrupt	INTO, INT1, INT3	I	INT interrupt input pins
Key input interrupt	KI0 to KI3	I	Key input interrupt input pins
Timer X	CNTR0	I/O	Timer X I/O pin
	CNTR0	0	Timer X output pin
Timer Z	TZOUT	0	Timer Z output pin
Timer C	TCIN	I	Timer C input pin
	CMP0_0 to CMP0_2, CMP1_0 to CMP1_2	0	Timer C output pins
Serial interface	CLK0	I/O	Transfer clock I/O pin
	RXD0, RXD1	I	Serial data input pins
	TXD0, TXD1	0	Serial data output pins
Reference voltage input	VREF	I	Reference voltage input pin to comparator
Comparator	AN8 to AN11	I	Analog input pins to comparator
I/O port	P1_0 to P1_7, P3_3 to P3_5, P3_7, P4_5	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. P1_0 to P1_3 also function as LED drive ports.
Input port	P4_2, P4_6, P4_7	I	Input-only ports

I: Input O: Output

I/O: Input and output

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.

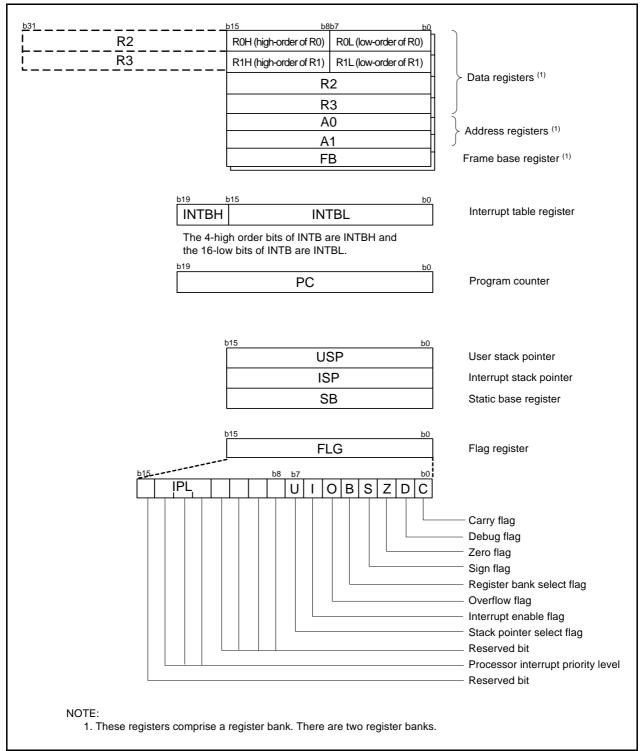


Figure 2.1 CPU Registers

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2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic and logic operations. A1 is analogous to A0. A1 can be combined with A0 and used as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the start address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide, indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointer (SP), USP, and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 **Carry Flag (C)**

The C flag retains a carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 **Zero Flag (Z)**

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when the operation results in an overflow; otherwise to 0.



2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts.

Interrupts are disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.

The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is 3 bits wide, assigns processor interrupt priority levels from level 0 to level 7. If a requested interrupt has higher priority than IPL, the interrupt is enabled.

2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.



3. Memory

3.1 R8C/18 Group

Figure 3.1 is a Memory Map of R8C/18 Group. The R8C/18 Group has 1 Mbyte of address space from addresses 00000h to FFFFFh.

The internal ROM area is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM is allocated addresses 0C000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.

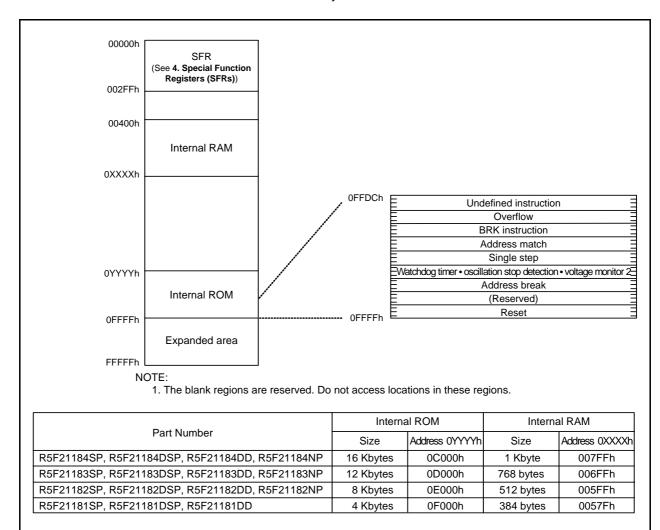


Figure 3.1 Memory Map of R8C/18 Group

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3.2 R8C/19 Group

Figure 3.2 is a Memory Map of R8C/19 Group. The R8C/19 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.

The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.

The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.

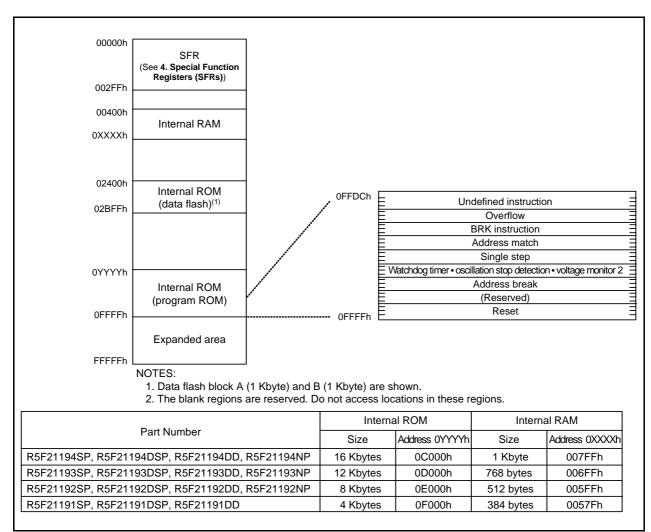


Figure 3.2 Memory Map of R8C/19 Group

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SFR Information (2)⁽¹⁾ Table 4.2

Address	Register	Symbol	After reset
0040h	5	,	
0041h			
0042h			
0043h			
0044h			
0045h			
0046h			
0047h			
0048h			
0049h			
004Ah			
004Bh			
004Ch			
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	Comparator Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh			
0050h	Compare 1 Interrupt Control Register	CMP1IC	XXXXX000b
0051h	UARTO Transmit Interrupt Control Register	SOTIC	XXXXX000b
0052h	UARTO Receive Interrupt Control Register	SORIC	XXXXX000b
0053h	UART1 Transmit Interrupt Control Register	S1TIC	XXXXX000b
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h	Timor V Interrupt Central Pagister	TVIC	VVVVV000h
0056h 0057h	Timer X Interrupt Control Register	TXIC	XXXXX000b
0057h 0058h	Timer Z Interrupt Control Register	TZIC	XXXXX000b
0059h	-	INT1IC	XXXXX000b
	INT1 Interrupt Control Register		
005Ah	INT3 Interrupt Control Register	INT3IC	XXXXX000b
005Bh	Timer C Interrupt Control Register	TCIC	XXXXX000b
005Ch	Compare 0 Interrupt Control Register	CMP0IC	XXXXX000b
005Dh	INTO Interrupt Control Register	INT0IC	XX00X000b
005Eh			
005Fh			
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h 0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h			
0073h			
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Cymahal	Parameter	Conditions		Lloit		
Symbol		Conditions	Min.	Тур.	Max.	Unit
=	Program/erase endurance ⁽²⁾	R8C/18 Group	100(3)	-	=	times
		R8C/19 Group	1,000(3)	-	-	times
-	Byte program time		ī	50	400	μS
=	Block erase time		-	0.4	9	S
td(SR-SUS)	Time delay from suspend request until suspend		=	=	97+CPU clock × 6 cycles	μS
_	Interval from erase start/restart until following suspend request		650	=	-	μS
_	Interval from program start/restart until following suspend request		0	=	-	ns
=	Time from suspend until program/erase restart		=	=	3+CPU clock × 4 cycles	μS
_	Program, erase voltage		2.7	_	5.5	V
-	Read voltage		2.7	-	5.5	V
=	Program, erase temperature		0	-	60	°C
=	Data hold time ⁽⁸⁾	Ambient temperature = 55 °C	20	-	=	year

NOTES:

- 1. Vcc = 2.7 to 5.5 V at Topr = 0 to 60 °C, unless otherwise specified.
- 2. Definition of programming/erasure endurance
 - The programming and erasure endurance is defined on a per-block basis.
 - If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
- 3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
- 4. If emergency processing is required, a suspend request can be generated independent of this characteristic. In that case the normal time delay to Suspend can be applied to the request. However, we recommend that a suspend request with an interval of less than 650 μs is only used once because, if the suspend state continues, erasure cannot operate and the incidence of erasure error rises.
- 5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the number of erase operations between block A and block B can further reduce the effective number of rewrites. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
- 6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
- 7. Customers desiring programming/erasure failure rate information should contact their Renesas technical support representative.
- 8. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.8 Reset Circuit Electrical Characteristics (When Using Voltage Monitor 1 Reset)

Symbol	Parameter	Condition	Standard		Unit	
			Min.	Тур.	Max.	
Vpor2	Power-on reset valid voltage	-20°C ≤ Topr ≤ 85°C	-	-	Vdet1	V
tw(Vpor2-Vdet1)	Supply voltage rising time when power-on reset is deasserted ⁽¹⁾	$\label{eq:continuous} \begin{array}{l} -20^{\circ}C \leq Topr \leq 85^{\circ}C, \\ t_{w(por2)} \geq 0s^{(3)} \end{array}$	I	I	100	ms

NOTES:

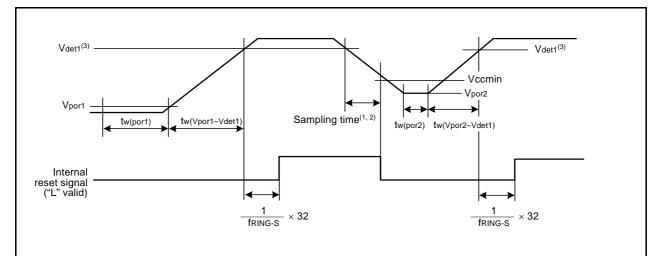
- 1. This condition is not applicable when using with $Vcc \ge 1.0 \text{ V}$.
- 2. When turning power on after the time to hold the external power below effective voltage (Vpor1) exceeds10 s, refer to Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset).
- 3. tw(por2) is the time to hold the external power below effective voltage (Vpor2).

Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset) Table 5.9

Symbol	Parameter	Condition		Standar	d	Unit
			Min.	Тур.	Max.	
Vpor1	Power-on reset valid voltage	-20°C ≤ Topr ≤ 85°C	=	=	0.1	V
tw(Vpor1-Vdet1)	Supply voltage rising time when power-on reset is deasserted	$0^{\circ}C \leq Topr \leq 85^{\circ}C,$ $tw(por1) \geq 10 s^{(2)}$	-	-	100	ms
tw(Vpor1-Vdet1)	Supply voltage rising time when power-on reset is deasserted	$ -20^{\circ}C \leq Topr < 0^{\circ}C, \\ tw(por1) \geq 30 \ s^{(2)} $	-	=	100	ms
tw(Vpor1-Vdet1)	Supply voltage rising time when power-on reset is deasserted	$ -20^{\circ}C \leq Topr < 0^{\circ}C, $ $ tw(por1) \geq 10 \ s^{(2)} $	-	=	1	ms
tw(Vpor1-Vdet1)	Supply voltage rising time when power-on reset is deasserted	$0^{\circ}C \leq Topr \leq 85^{\circ}C,$ $tw(por1) \geq 1 s^{(2)}$	-	-	0.5	ms

NOTES:

- 1. When not using voltage monitor 1, use with $Vcc \ge 2.7 \text{ V}$.
- 2. tw(por1) is the time to hold the external power below effective voltage (Vpor1).



NOTES:

- 1. Hold the voltage inside the MCU operation voltage range (Vccmin or above) within the sampling time.
- The sampling clock can be selected. Refer to 7. Voltage Detection Circuit for details.
 Vdet1 indicates the voltage detection level of the voltage detection 1 circuit. Refer to 7. Voltage Detection Circuit for details.

Figure 5.3 **Reset Circuit Electrical Characteristics**

Table 5.13 Electrical Characteristics (2) [Vcc = 5 V] (Topr = -40 to 85 $^{\circ}$ C, unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
Cymbol	1 didiliotoi			Min.	Тур.	Max.	01110
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open,	High-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	I	9	15	mA
	other pins are Vss, comparator is stopped		XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	-	8	14	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	-	5	ı	mA
		Medium- speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	I	4	1	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	-	3	_	mA
		XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	1	2	-	mA	
		High-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz No division	-	4	8	mA
			Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	ı	1.5	ı	mA
		Low-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8 FMR47 = 1	1	110	300	μА
	Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = 0	-	40	80	μА	
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = 0	_	38	76	μА
		Stop mode	Main clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = 0	_	0.8	3.0	μА

Timing Requirements

(Unless Otherwise Specified: Vcc = 5 V, Vss = 0 V at Ta = 25 °C) [Vcc = 5 V]

Table 5.14 XIN Input

Symbol	Parameter —		Standard	
Symbol			Max.	Unit
tc(XIN)	XIN input cycle time	50	=	ns
twh(xin)	XIN input "H" width	25	-	ns
twl(XIN)	XIN input "L" width	25	-	ns

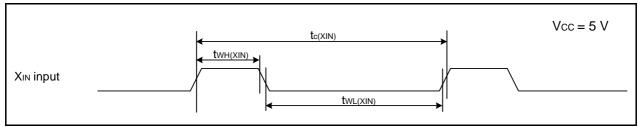


Figure 5.4 XIN Input Timing Diagram when Vcc = 5 V

Table 5.15 CNTR0 Input, CNTR1 Input, INT1 Input

Symbol	Parameter		Standard	
Symbol			Max.	Unit
tc(CNTR0)	CNTR0 input cycle time	100	=	ns
tWH(CNTR0)	CNTR0 input "H" width	40	=	ns
tWL(CNTR0)	CNTR0 input "L" width	40		ns

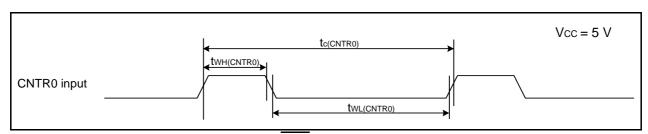


Figure 5.5 CNTR0 Input, CNTR1 Input, INT1 Input Timing Diagram when Vcc = 5 V

Table 5.16 TCIN Input, INT3 Input

Symbol	Parameter –		Standard		
Symbol			Max.	Unit	
tc(TCIN)	TCIN input cycle time	400 ⁽¹⁾	-	ns	
tWH(TCIN)	TCIN input "H" width	200(2)	-	ns	
tWL(TCIN)	TCIN input "L" width	200(2)	I	ns	

NOTES:

- 1. When using timer C input capture mode, adjust the cycle time to (1/timer C count source frequency x 3) or above.
- 2. When using timer C input capture mode, adjust the pulse width to (1/timer C count source frequency x 1.5) or above.

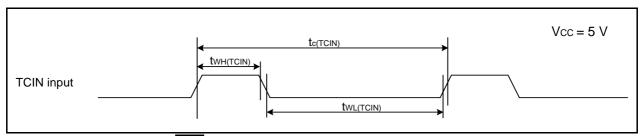


Figure 5.6 TCIN Input, INT3 Input Timing Diagram when Vcc = 5 V

Table 5.17 Senai illenace	Table	5.17	Serial	Interface
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Symbol	Parameter		Standard		
	raianielei	Min.	Max.	Unit	
tc(CK)	CLKi input cycle time	200	-	ns	
tW(CKH)	CLKi input "H" width	100	=	ns	
tW(CKL)	CLKi input "L" width		=	ns	
td(C-Q)	TXDi output delay time	-	50	ns	
th(C-Q)	TXDi hold time	0	-	ns	
tsu(D-C)	RXDi input setup time	50	=	ns	
th(C-D)	RXDi input hold time	90	-	ns	

i = 0 or 1

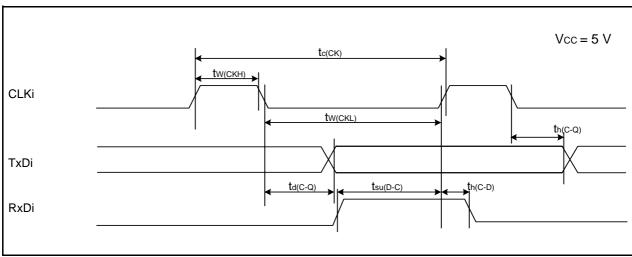


Figure 5.7 Serial Interface Timing Diagram when Vcc = 5 V

Table 5.18 External Interrupt INTO Input

Symbol	Parameter		Standard		
			Max.	Unit	
tW(INH)	INTO input "H" width	250 ⁽¹⁾	-	ns	
tW(INL)	INTO input "L" width	250(2)	-	ns	

NOTES:

- 1. When selecting the digital filter by the INT0 input filter select bit, use an INT0 input HIGH width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater.
- 2. When selecting the digital filter by the INT0 input filter select bit, use an INT0 input LOW width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater.

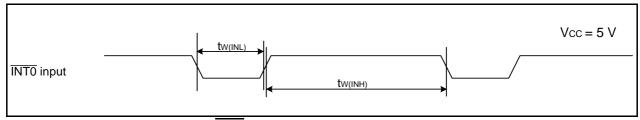


Figure 5.8 External Interrupt INTO Input Timing Diagram when Vcc = 5 V

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Electrical Characteristics (3) [Vcc = 3V] **Table 5.19**

Symbol	Parameter		Condition		Standard			Unit
Symbol					Min.	Тур.	Max.	Unit
Vон	Output "H" voltage	Except Xouт	Iон = -1 mA		Vcc - 0.5	_	Vcc	V
		Хоит	Drive capacity HIGH	IOH = -0.1 mA	Vcc - 0.5	-	Vcc	V
			Drive capacity LOW	Іон = -50 μΑ	Vcc - 0.5	_	Vcc	V
Vol	Output "L" voltage	Except P1_0 to P1_3, Xout	IOL = 1mA		-	=	0.5	V
		P1_0 to P1_3	Drive capacity HIGH	IOL = 2 mA	-	_	0.5	V
			Drive capacity LOW	IOL = 1 mA	-	_	0.5	V
		Хоит	Drive capacity HIGH	IOL = 0.1 mA	=	-	0.5	V
			Drive capacity LOW	IOL = 50 μA	-	-	0.5	V
VT+-VT-	Hysteresis	INTO, INT1, INT2, INT3, KIO, KI1, KI2, KI3, CNTRO, CNTR1, TCIN, RXD0			0.2	-	0.8	V
		RESET			0.2	-	1.8	V
Іін	Input "H" current	•	VI = 3 V		-	-	4.0	μΑ
lıL	Input "L" current		VI = 0 V		-	-	-4.0	μΑ
RPULLUP	Pull-up resistance		VI = 0 V		66	160	500	kΩ
RfXIN	Feedback resistance	XIN			=	3.0	=	ΜΩ
fring-s	Low-speed on-chip os	cillator frequency			40	125	250	kHz
VRAM	RAM hold voltage		During stop mode		2.0	-	-	V

NOTE:

^{1.} Vcc = 2.7 to 3.3 V at Topr = -20 to 85 °C / -40 to 85 °C, f(XIN) = 10 MHz, unless otherwise specified.

Electrical Characteristics (4) [Vcc = 3V] (Topr = -40 to 85 °C, unless otherwise specified.) **Table 5.20**

Symbol	Parameter	Condition			Standard Min. Typ. Max.			
Cymbol	i didiliotoi	Condition			Тур.	Max.	Unit	
Icc	Power supply current (Vcc = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are Vss, comparator is stopped	High-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	ı	8	13	mA	
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	ſ	7	12	mA	
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	_	5	ı	mA	
		Medium- speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	-	3		mA	
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	I	2.5	_	mA	
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	_	1.6	-	mA	
		High-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz No division	_	3.5	7.5	mA	
			Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	_	1.5	-	mA	
		Low-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8 FMR47 = 1	-	100	280	μΑ	
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = 0	-	37	74	μΑ	
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = 0	=	35	70	μА	
		Stop mode	Main clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = 0	-	0.7	3.0	μΑ	

REVISION HISTORY

R8C/18 Group, R8C/19 Group Datasheet

Boy	Doto	Description			
Rev.	Date	Page	Summary		
0.10	Nov 15, 2004	-	First Edition issued		
0.20	Jan 11, 2005	5, 6	Tables 1.3 and 1.4: The date updated		
0.21	Apr 04, 2005	2, 3	Tables 1.1 and 1.2: Partly revised		
		4	Figure 1.1: Partly revised		
		5, 6	Tables 1.3 and 1.4: Partly revised		
		5, 6	Figure 1.2 and 1.3: Partly revised		
		7, 8	Figure 1.4 and 1.5: Partly revised		
		10	Table 1.6: Partly revised		
		16	Table 4.1: Partly revised		
		17	Table 4.2: Partly revised		
		18	Table 4.3: Partly revised		
		20	Package Dimensions are revised		
1.00	May 27, 2005	5, 6	Tables 1.3 and 1.4: Partly revised		
		9	Table 1.5: Partly revised		
		25	Table 5.9: Revised		
		26	Table 5.10: Partly revised		
		28	Table 5.13: Partly revised		
		32	Table 5.20: Partly revised		
1.10	Jun 09, 2005	26	Table 5.10: Partly revised		
1.20	Nov 01, 2005	3	Table 1.2 Performance Outline of the R8C/19 Group; Flash Memory: (Data area) → (Data flash) (Program area) → (Program ROM) revised		
		4	Figure 1.1 Block Diagram; "Peripheral Function" added, "System Clock Generation" → "System Clock Generator" revised		
		6	Table 1.4 Product Information of R8C/19 Group; ROM capacity: "Program area" → "Program ROM", "Data area" → "Data flash" revised		
		9	Table 1.5 Pin Description; Power Supply Input: "VCC/AVCC" → "VCC", "VSS/AVSS" → "VSS" revised Analog Power Supply Input: added		
		11	Figure 2.1 CPU Register; "Reserved Area" → "Reserved Bit" revised		
		13	2.8.10 Reserved Area; "Reserved Area" → "Reserved Bit" revised		
		15	3.2 R8C/19 Group, Figure 3.2 Memory Map of R8C/19 Group; "Data area" → "Data flash", "Program area" → "Program ROM" revised		

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